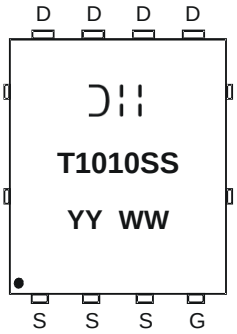
Marking Information



= Manufacturer's Marking
T1010SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year
(ex: 17 = 2017)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	9.4 7.5	A
	Steady State	T_C = +25°C T_C = +100°C	I_D	98 62	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	250	A
Maximum Continuous Body Diode Forward Current			I_S	110	A
Pulsed Body Diode Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	250	A
Avalanche Current (Note 7), L=3mH			I_{AS}	10	A
Avalanche Energy (Note 7), L=3mH			E_{AS}	150	mJ
V_{DS} Spike, L=0.1mH		t = 10µs	V_{SPIKE}	110	V

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	99	°C/W
Total Power Dissipation	T_C = +25°C	P_D	139	W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	0.9	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	1.9	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6.9	8.3	mΩ	V_{GS} = 10V, I_D = 13A
		—	7.5	12		V_{GS} = 6V, I_D = 13A
		—	10	20		V_{GS} = 4.5V, I_D = 5A
Diode Forward Voltage	V_{SD}	—	0.8	1.3	V	V_{GS} = 0V, I_S = 13A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	2592	—	pF	V_{DS} = 50V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	792	—		
Reverse Transfer Capacitance	C_{rss}	—	45	—		
Gate Resistance	R_g	—	2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	53.7	—	nC	V_{DD} = 50V, I_D = 13A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	10.6	—		
Gate-Drain Charge	Q_{gd}	—	8.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	11.6	—	ns	V_{DD} = 50V, V_{GS} = 10V, I_D = 13A, R_g = 6Ω
Turn-On Rise Time	t_R	—	14.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	42.9	—		
Turn-Off Fall Time	t_F	—	22	—		
Reverse Recovery Time	t_{RR}	—	49.8	—	ns	I_F = 13A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	85.1	—	nC	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

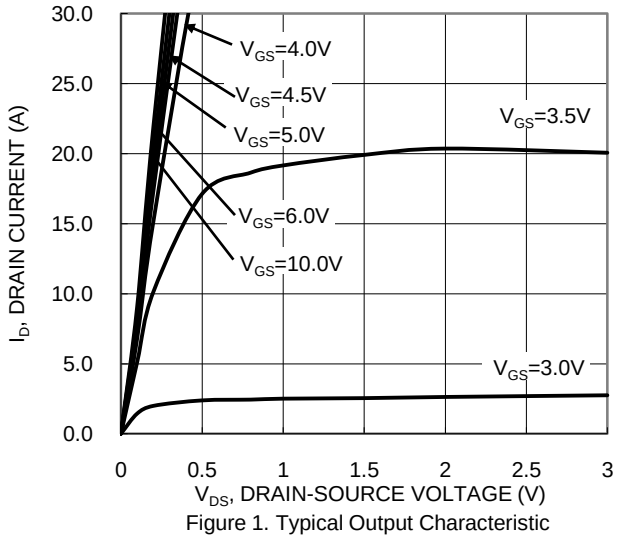


Figure 1. Typical Output Characteristic

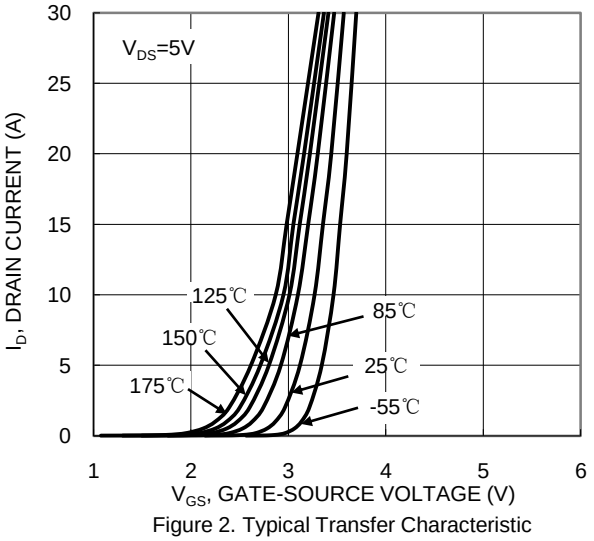


Figure 2. Typical Transfer Characteristic

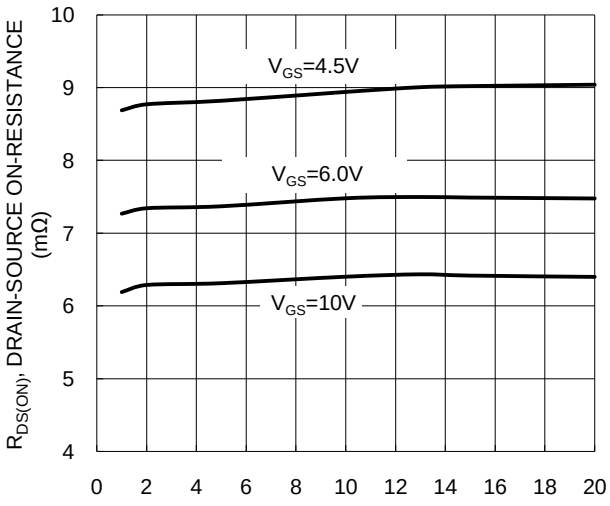


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

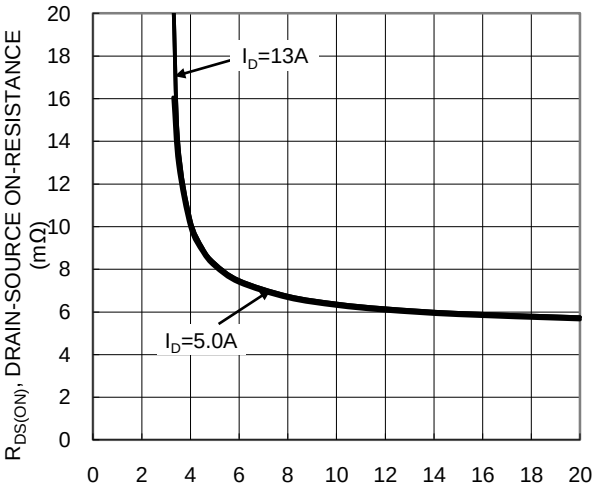


Figure 4. Typical Transfer Characteristic

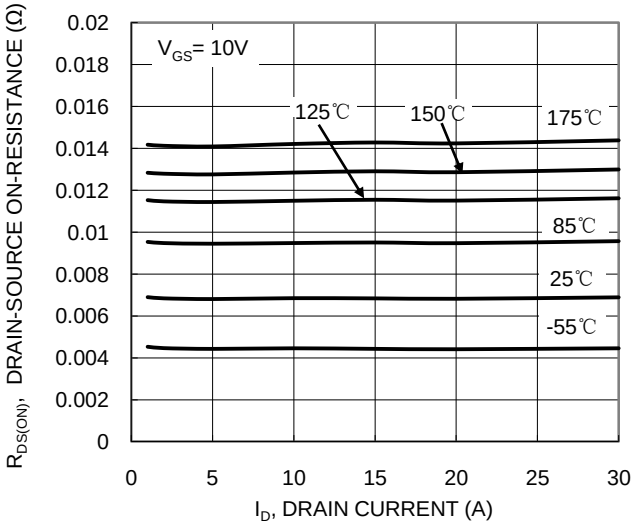


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

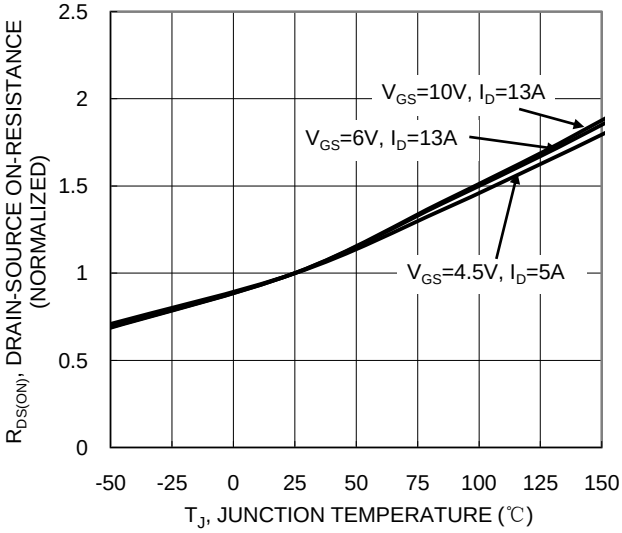


Figure 6. On-Resistance Variation with Temperature

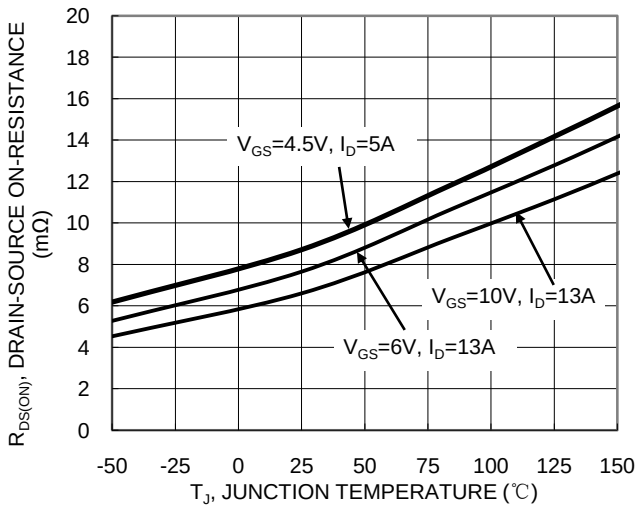


Figure 7. On-Resistance Variation with Temperature

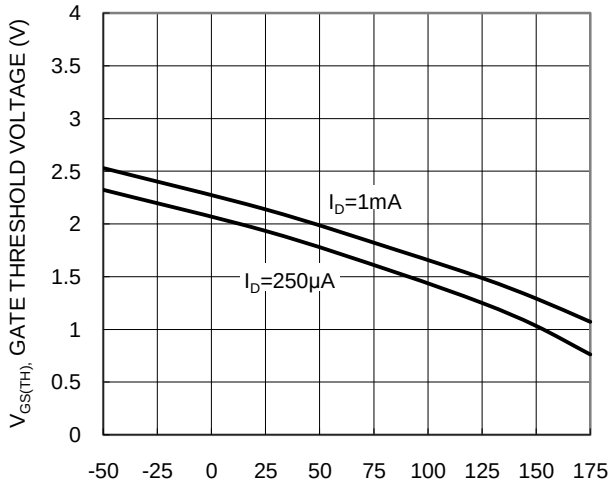


Figure 8. Gate Threshold Variation vs. Junction Temperature

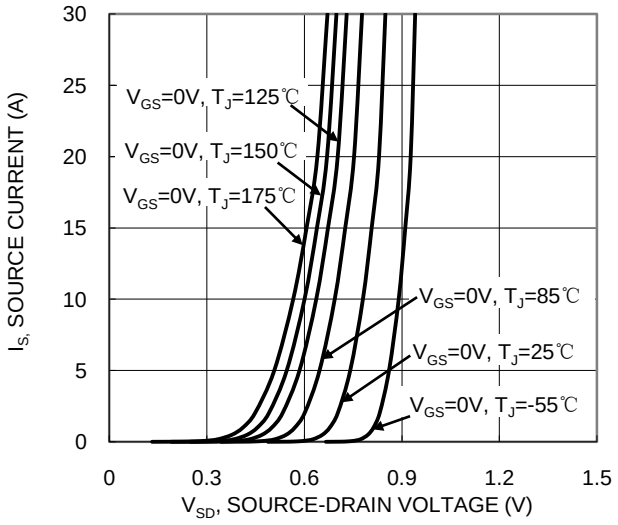


Figure 9. Diode Forward Voltage vs Current

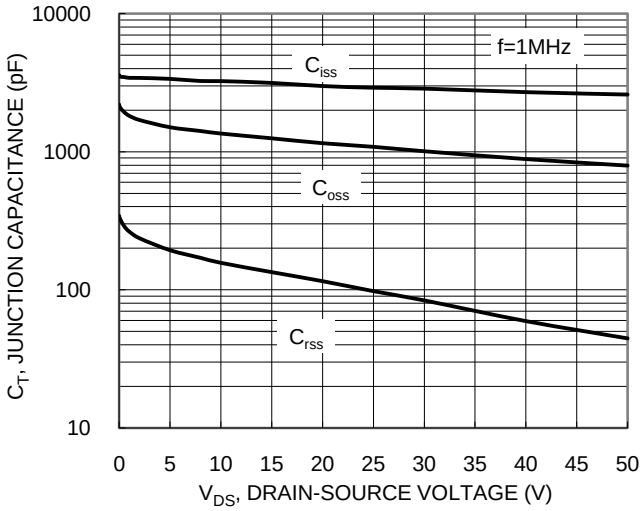


Figure 10. Typical Junction Capacitance

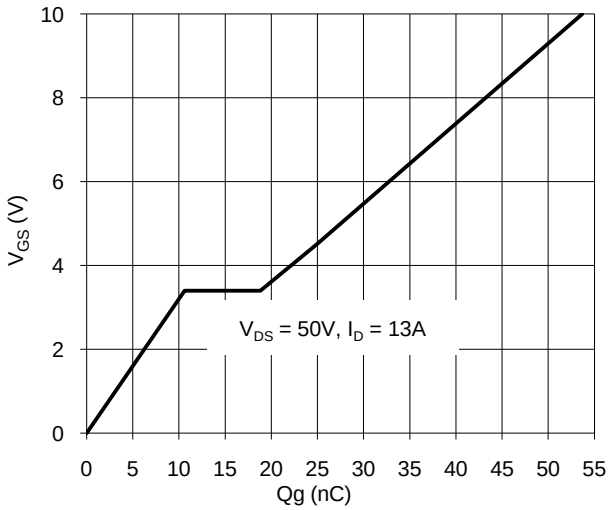


Figure 11. Gate Charge

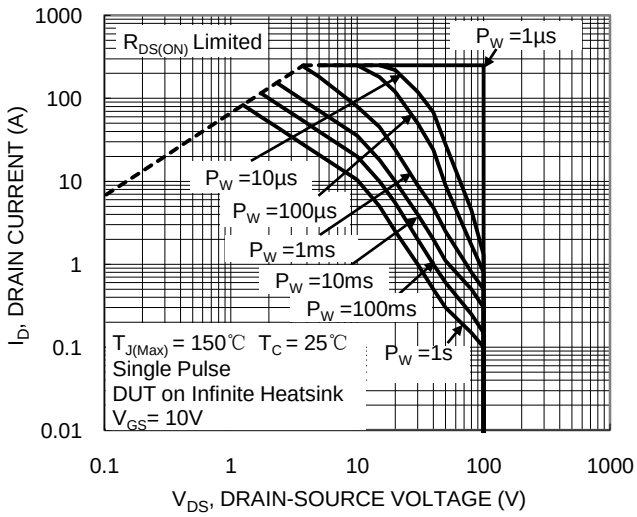


Figure 12. SOA, Safe Operation Area

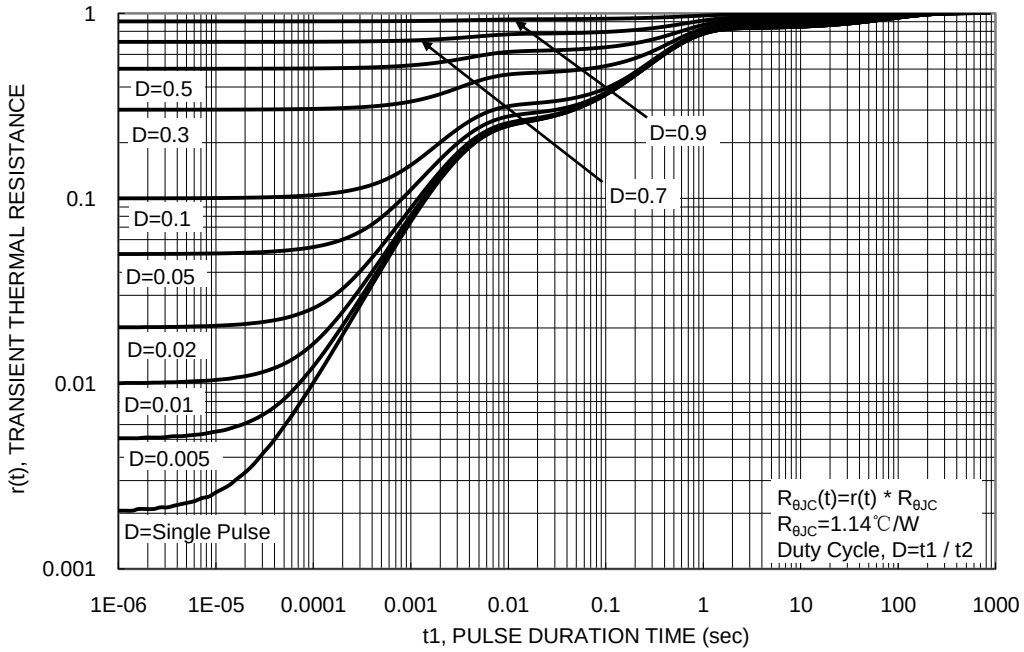
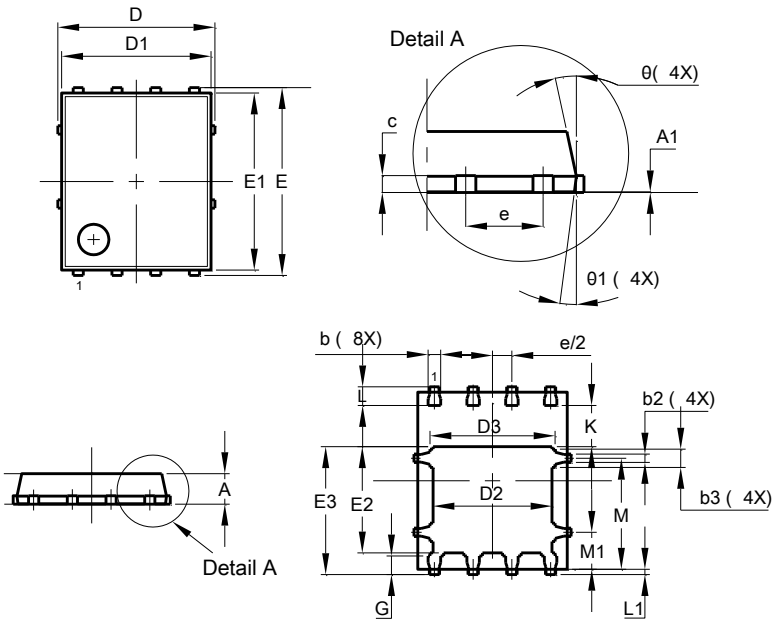


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

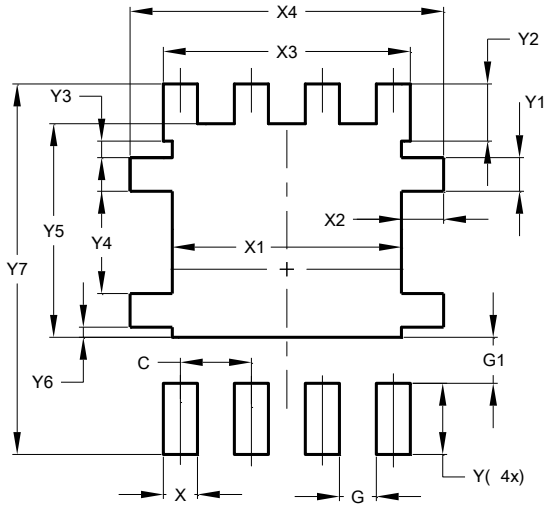


PowerDI5060-8			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0.00	0.05	–
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	–	–
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
Θ	10°	12°	11°
Θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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